

N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK88

10 January 2025

Product data sheet

1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a copper-clip LFPAK88 package. This product has been fully designed and qualified to meet beyond AEC-Q101 requirements delivering high performance and reliability.

2. Features and benefits

- Fully automotive qualified to beyond AEC-Q101:
- -55 °C to +175 °C rating suitable for thermally demanding environments
- LFPAK88 package:
 - Designed for smaller footprint and improved power density over older wire bond packages such as D²PAK for today's space constrained high power automotive applications
 - Thin package and copper clip enables LFPAK88 to be highly efficient thermally
- LFPAK copper clip technology enabling improvements over wire bond packages by:
 - Increased maximum current capability and excellent current spreading
 - Improved R_{DSon}
 - Low source inductance
 - Low thermal resistance R_{th}
- LFPAK Gull Wing leads:
 - Flexible leads enabling high Board Level Reliability absorbing mechanical and thermal cycling stress, unlike traditional QFN packages
 - · Visual (AOI) soldering inspection, no need for expensive x-ray equipment
 - Easy solder wetting for good mechanical solder joint
- Unique 40 V Trench 9 superjunction technology:
 - Reduced cell pitch and superjunction platform enables lower R_{DSon} in the same footprint
 - Improved SOA and avalanche capability compared to standard TrenchMOS
 - Tight V_{GS(th)} limits enable easy paralleling of MOSFETs

3. Applications

- 12 V automotive systems
- 48 V DC/DC systems (on 12 V secondary side)
- Higher power motors, lamps and solenoid control
- Reverse polarity protection
- LED lighting
- Ultra high performance power switching

4. Quick reference data

Symbol	k reference data Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	325	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	375	W

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	acteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12		0.62	0.88	1	mΩ
Dynamic ch	naracteristics						
Q _{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 32 V; V _{GS} = 10 V; Fig. 14; Fig. 15		-	17	34	nC
Source-dra	in diode						
Qr	recovered charge		[2]	-	49	-	nC
S	softness factor	$ I_{S} = 25 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; T_{j} = 25 ^{\circ}\text{C} $		-	0.8	-	

This current had been successfully demonstrated during product characterisation. In practical applications the current will be limited by [1] PCB, thermal design and operating temperature.

includes capacitive recovery [2]

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source		D
3	S	source	0	
4	S	source		G_(↓ĘŢ本)
mb	D	mounting base; connected to drain	LFPAK88 (SOT1235)	mbb076 S

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BUK7S1R0-40H	LFPAK88	plastic, single-ended surface-mounted package (LFPAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body	<u>SOT1235</u>				

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7S1R0-40H	7S1R040H

BUK7S1R0-40H

N-channel 40 V, 1.0 mQ standard level MOSFET in LFPAK88

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Tj = 25 °C unless otherwise stated.

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	V
V _{GS}	gate-source voltage		[1]	-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	375	W
ID	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[2]	-	325	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C; <u>Fig. 3;</u> <u>Fig. 4</u>	[2]	-	1659	A
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	n diode					
I _S	source current	T _{mb} = 25 °C	[2]	-	350	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1659	А
Avalanche r	uggedness					
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$ \begin{array}{l} I_D = 120 \text{ A}; \ V_{sup} \leq \ 40 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 10 \text{ V}; \ T_{j(init)} = 25 \ ^\circ\text{C}; \ unclamped; \\ \hline \hline Fig. \ 5 \end{array} $	[3] [4]	-	437	mJ

[1] Refer to application note AN90001 for further information.

[2] This current had been successfully demonstrated during product characterisation. In practical applications the current will be limited by PCB, thermal design and operating temperature.

[3] Single pulse avalanche rating limited by maximum junction temperature of 175°C.

[4] Refer to application note AN10273 for further information.

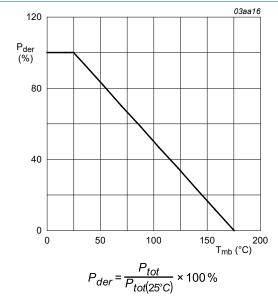
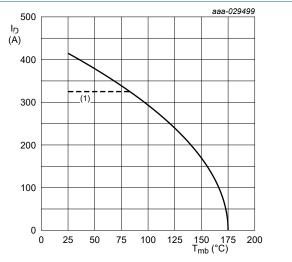


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

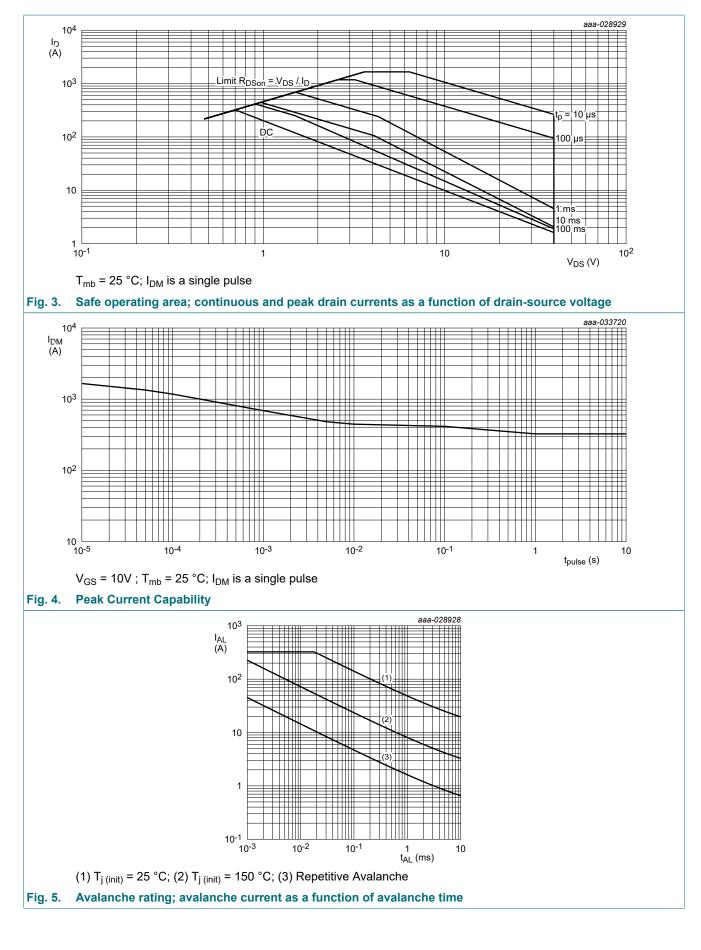


 $V_{GS} \ge 10 V$

(1) 325A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature

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9. Thermal characteristics

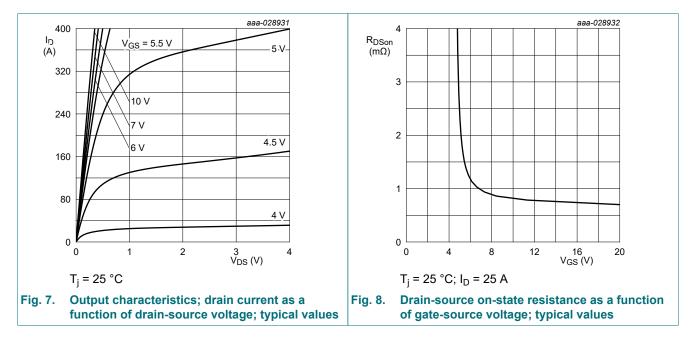
Table 6. Thermal characteristics Symbol Conditions Unit Parameter Min Тур Max thermal resistance from Fig. 6 0.35 K/W 0.4 $R_{th(j-mb)}$ junction to mounting base aaa-028930 1 Z_{th(i-mb)} (K/W) # δ = 0.5 10⁻¹ 0:2= 0:1= 0.05 tp 0:02 single sho Р 10⁻² ₩ δ= Т t tp т 10⁻³ 10⁻⁶ 10⁻³ 10⁻² 10⁻⁵ 10-4 10⁻¹ 1 t_p (s) Transient thermal impedance from junction to mounting base as a function of pulse duration Fig. 6.

10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	cteristics	, ,	I			
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	40	43	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -40 °C	-	40.5	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	36	40	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 10; Fig. 11$	2.4	3	3.6	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 11</u>	1	-	-	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; <u>Fig. 11</u>	-	-	4.3	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.2	1.5	μA
		V _{DS} = 16 V; V _{GS} = 0 V; T _j = 125 °C	-	4.7	25	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	287	1000	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _i = 25 °C	-	2	100	nA

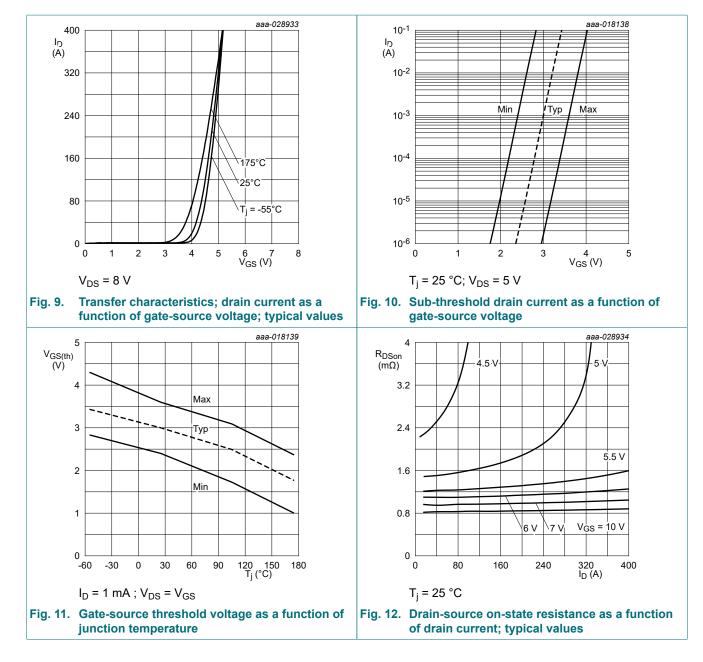
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12		0.62	0.88	1	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 105 °C; Fig. 13		0.87	1.3	1.6	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 125 °C; Fig. 13		0.97	1.4	1.75	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 13		1.2	1.8	2.2	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C		0.4	0.9	2.3	Ω
Dynamic ch	naracteristics						
Q _{G(tot)}	total gate charge	I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V;		-	98	137	nC
Q _{GS}	gate-source charge	Fig. 14; Fig. 15		-	27	40	nC
Q _{GD}	gate-drain charge			-	17	34	nC
C _{iss}	input capacitance	$V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;$ T _j = 25 °C; Fig. 16		-	7373	10322	pF
C _{oss}	output capacitance			-	1578	2209	pF
C _{rss}	reverse transfer capacitance			-	295	649	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 10 V;		-	23	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$		-	19	-	ns
t _{d(off)}	turn-off delay time			-	59	-	ns
t _f	fall time			-	26	-	ns
Source-drai	in diode						
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 17</u>		-	0.76	1	V
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$		-	43	-	ns
Q _r	recovered charge	V _{DS} = 20 V	[1]	-	49	-	nC
S	softness factor	$I_{S} = 25 \text{ A}; \text{ d}_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$		-	0.8	-	
		$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -500 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $\text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 ^{\circ}\text{C}$		-	0.7	-	

[1] includes capacitive recovery



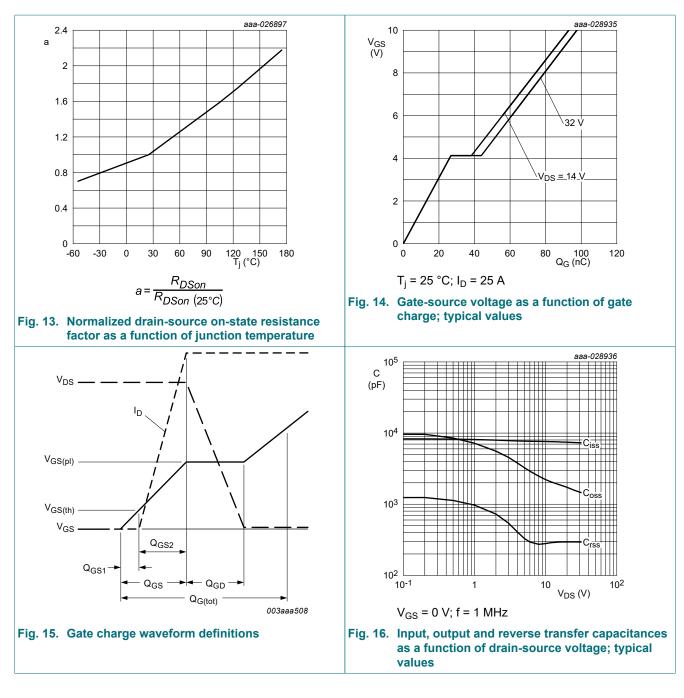
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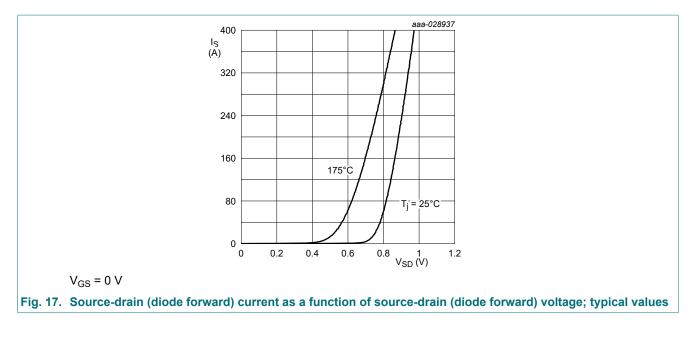
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Product data sheet

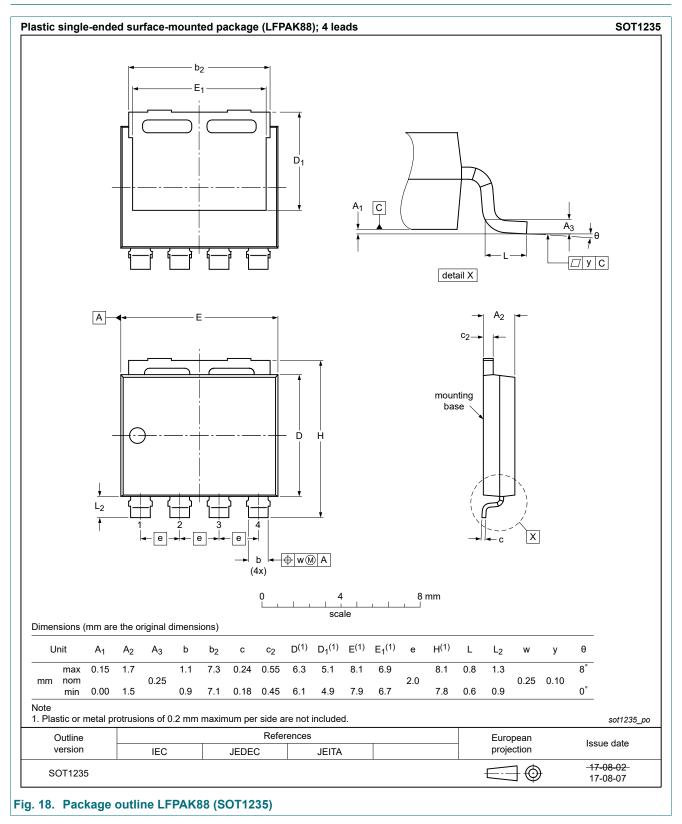
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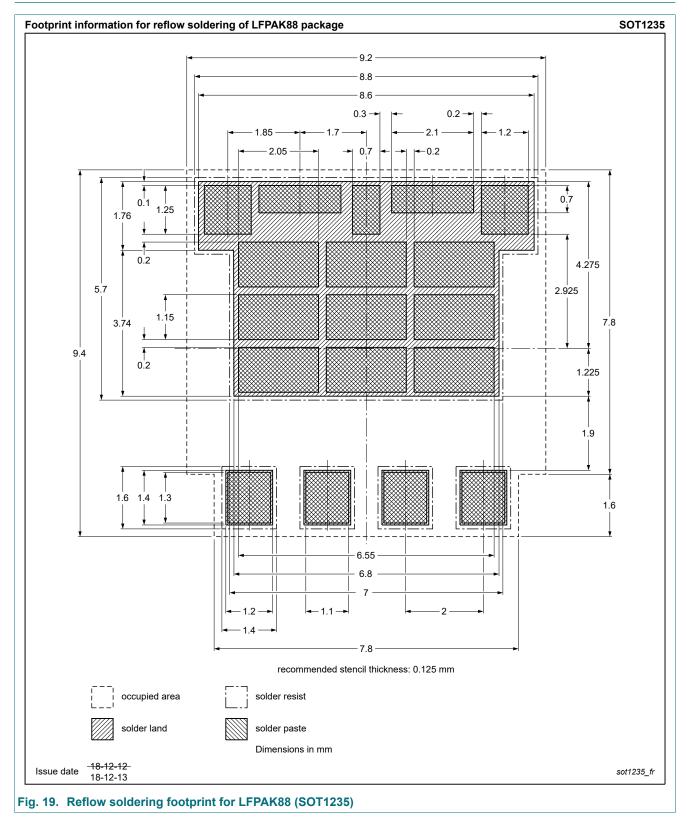
N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK88

11. Package outline



N-channel 40 V, 1.0 m Ω standard level MOSFET in LFPAK88

12. Soldering



N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK88

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	5
10.	Characteristics	5
11.	Package outline	10
12.	Soldering	11
	Legal information	
	-	

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